

AMENDMENTS

(Japanese Law Section 11 based on PCT Article 34 (2)(b))

To : Examiner of the Patent Office, Misako ANZAI

1. Identification of the International Application
PCT/JP2005/002560

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4. Item to be amended
Claims

5. Subject matter of amendments

As per the attached paper, we amend the claims. The amendments are as follows.

The limitations that “the source gas includes at least one of nitrogen and ammonia, and the other materials include at least one Group III element selected from the group consisting of gallium, aluminum, and indium and a flux material” and that “the single crystal is a Group III nitride single crystal” have been added to claim 1.

Accordingly, claim 13 has been canceled.

With the cancellation of claim 13, claims 14 and 23-25 have been amended to depend from claim 1, and claim 15 has been amended to depend

from claim 2.

6. List of attached documents

(1) A new sheet for pages 31, 32, and 33 of claims (translation: pages 39, 39/1, 40 and 41 of claims) 1

CLAIMS

[1] (Amended) A method for producing a compound single crystal comprising:

growing a compound single crystal by reacting a source gas with a material solution including other materials,

wherein the source gas includes at least one of nitrogen and ammonia, and the other materials include at least one Group III element selected from the group consisting of gallium, aluminum, and indium and a flux material, and

wherein a Group III nitride single crystal is grown while stirring the material solution to create a flow from a gas-liquid interface in contact with the source gas toward an inside of the material solution.

[2] The method according to claim 1, using a single crystal production apparatus comprising a heating unit and a closed pressure- and heat-resistant container that is heated inside the heating unit,

wherein the source gas of the compound single crystal and other materials are provided to the container and sealed in a pressurized atmosphere,

the container is housed in the heating unit,

a material solution is prepared by heating the container in the heating unit so that the other materials melt into a liquid, and

under these conditions, a single crystal is grown by reacting the source gas with the material solution while the material solution is stirred.

[3] The method according to claim 2, wherein the single crystal is grown by reacting the source gas with the material solution while the material solution is stirred by rocking the container.

[4] The method according to claim 3, wherein the container is rocked by rocking the heating unit.

[5] The method according to claim 2, wherein a crucible is set in the container, and at least one of an inside and an inner wall of the crucible has

at least one selected from the group consisting of (A) impeller, (B) baffle, (C) template, and (D) helical protrusions.

[6] The method according to claim 3, wherein the rocking is at least one selected from the group consisting of a shift motion, a linear repetitive motion, a pendular motion, a rotational motion, and a combined motion of any of

these motions.

[7] The method according to claim 2, wherein the other materials include a flux material.

[8] The method according to claim 3, wherein the single crystal production apparatus further comprises a source gas supply unit,
the source gas supply unit is connected to the container in which the other materials have been put, supplies the source gas to the container, and is separated from the container after supplying the source gas, and subsequently the container is rocked.

[9] The method according to claim 8, wherein the source gas supply unit is separated from the container after heating the container so that the other materials melt into a liquid and adjusting a pressure in the container.

[10] The method according to claim 2, wherein a pressure of the source gas in the container is reduced after formation of the single crystal.

[11] The method according to claim 2, wherein the single crystal production apparatus further comprises an auxiliary tank system for supplying the source gas, and the auxiliary tank system is connected to the container.

[12] The method according to claim 3, wherein the single crystal production apparatus further comprises a source gas supply unit, the source gas supply unit and the container are connected by a flexible pipe, and the container is rocked without being separated from the source gas supply unit.

[13] (Canceled)

[14] (Amended) The method according to claim 1, wherein the flux material includes at least one of an alkali metal and alkaline-earth metal.

[15] (Amended) The method according to claim 2, wherein a template that comprises a semiconductor layer expressed as a composition formula: $\text{Al}_u\text{Ga}_v\text{In}_{1-u-v}\text{N}$ ($0 \leq u \leq 1$, $0 \leq v \leq 1$, and $0 \leq u + v \leq 1$) is placed in the container beforehand.

[16] The method according to claim 15, wherein the material solution is

prepared by heating in the container, the source gas is dissolved in the material solution, and subsequently the template is immersed in the material solution.

[17] The method according to claim 15, wherein a crucible is set in the container, and the template is a sheet template and placed substantially upright on a bottom of the crucible.

[18] The method according to claim 17, wherein the container is rocked so that the material solution moves parallel to the sheet template.

[19] The method according to claim 7, wherein at least the flux material is removed from the container after the growth of the compound single crystal is finished.

[20] The method according to claim 19, wherein the material solution includes at least gallium and sodium, and a heating temperature of the material solution is 100°C (373 K) or more.

[21] The method according to claim 20, wherein the heating temperature is 300°C (573 K) or more.

[22] The method according to claim 20, wherein the heating temperature is 500°C (773 K) or more.

[23] (Amended) The method according to claim 1, wherein a growth rate of the Group III nitride single crystal is 30 $\mu\text{m}/\text{hour}$ or more.

[24] (Amended) The method according to claim 1, wherein a growth rate of the Group III nitride single crystal is 50 $\mu\text{m}/\text{hour}$ or more.

[25] (Amended) The method according to claim 1, wherein a growth rate of the Group III nitride single crystal is 100 $\mu\text{m}/\text{hour}$ or more.

[26] The method according to claim 2, wherein a pressure of the source gas in the container is 5 atm ($5 \times 1.01325 \times 10^5 \text{ Pa}$) to 1000 atm ($1000 \times 1.01325 \times 10^5 \text{ Pa}$).